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# DISCRETE SEMICONDUCTORS

# DATA SHEET

# **BFR93AW**NPN 5 GHz wideband transistor

Product specification Supersedes data of November 1992 1995 Sep 18



# NPN 5 GHz wideband transistor

# **BFR93AW**

#### **FEATURES**

- High power gain
- Gold metallization ensures excellent reliability
- SOT323 (S-mini) package.

#### **APPLICATIONS**

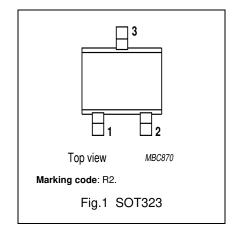
It is designed for use in RF amplifiers, mixers and oscillators with signal frequencies up to 1 GHz.

#### **DESCRIPTION**

Silicon NPN transistor encapsulated in a plastic SOT323 (S-mini) package. The BFR93AW uses the same crystal as the SOT23 version, BFR93A.

#### **PINNING**

| PIN | DESCRIPTION |  |  |
|-----|-------------|--|--|
| 1   | base        |  |  |
| 2   | emitter     |  |  |
| 3   | collector   |  |  |



#### **QUICK REFERENCE DATA**

| SYMBOL           | PARAMETER                     | CONDITIONS   | MIN. | TYP. | MAX. | UNIT |
|------------------|-------------------------------|--|------|------|------|------|
| V <sub>CBO</sub> | collector-base voltage        | open emitter   | _    | _    | 15   | V    |
| V <sub>CEO</sub> | collector-emitter voltage     | open base  | _    | _    | 12   | V    |
| Ic               | collector current (DC)        |  | -    | _    | 35   | mA   |
| P <sub>tot</sub> | total power dissipation       | up to T <sub>s</sub> = 93 °C; note 1   | _    | _    | 300  | mW   |
| h <sub>FE</sub>  | DC current gain               | $I_C = 30 \text{ mA}; V_{CE} = 5 \text{ V}$  | 40   | 90   | _    |      |
| C <sub>re</sub>  | feedback capacitance          | $I_{C} = 0$ ; $V_{CE} = 5 \text{ V}$ ; $f = 1 \text{ MHz}$ ; $T_{amb} = 25 \text{ °C}$       | _    | 0.6  | _    | pF   |
| f <sub>T</sub>   | transition frequency          | $I_C = 30 \text{ mA}; V_{CE} = 5 \text{ V}; f = 500 \text{ MHz}$                             | 4    | 5    | _    | GHz  |
| G <sub>UM</sub>  | maximum unilateral power gain | $I_C = 30 \text{ mA}; V_{CE} = 8 \text{ V}; f = 1 \text{ GHz};$<br>$T_{amb} = 25 \text{ °C}$ | _    | 13   | _    | dB   |
|                  |                               | $I_C = 30 \text{ mA}; V_{CE} = 8 \text{ V}; f = 2 \text{ GHz}; $ $T_{amb} = 25 \text{ °C}$   | _    | 8    | _    | dB   |
| F                | noise figure                  | $I_C$ = 5 mA; $V_{CE}$ = 8 V; f = 1 GHz; $\Gamma_s = \Gamma_{opt}$                           | _    | 1.5  | _    | dB   |
| T <sub>j</sub>   | junction temperature          |  | _    | _    | 150  | °C   |

#### Note

1.  $T_s$  is the temperature at the soldering point of the collector pin.

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#### **LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 134).

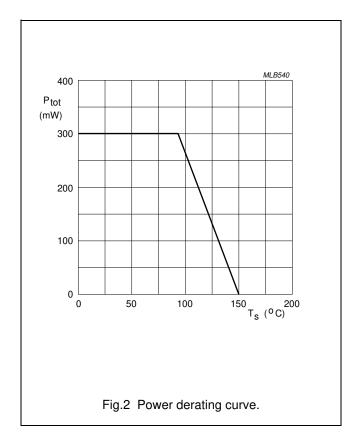
| SYMBOL           | PARAMETER                 | CONDITION                                       | MIN. | MAX. | UNIT |
|------------------|---------------------------|---|------|------|------|
| V <sub>CBO</sub> | collector-base voltage    | open emitter                                    | _    | 15   | V    |
| $V_{CEO}$        | collector-emitter voltage | open base                                       | _    | 12   | V    |
| V <sub>EBO</sub> | emitter-base voltage      | open collector                                  | _    | 2    | V    |
| Ic               | collector current (DC)    |   | _    | 35   | mA   |
| P <sub>tot</sub> | total power dissipation   | up to T <sub>s</sub> = 93 °C; see Fig.2; note 1 | _    | 300  | mW   |
| T <sub>stg</sub> | storage temperature       |   | -65  | +150 | °C   |
| Tj               | junction temperature      |   | _    | 150  | °C   |

#### THERMAL CHARACTERISTICS

| SYMBOL              | PARAMETER   | CONDITION                            | VALUE | UNIT |
|---------------------|---|--------------------------------------|-------|------|
| R <sub>th j-s</sub> | thermal resistance from junction to soldering point | up to T <sub>s</sub> = 93 °C; note 1 | 190   | K/W  |

#### Note to the Limiting values and Thermal characteristics

1.  $T_s$  is the temperature at the soldering point of the collector pin.



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#### **CHARACTERISTICS**

 $T_j$  = 25 °C (unless otherwise specified).

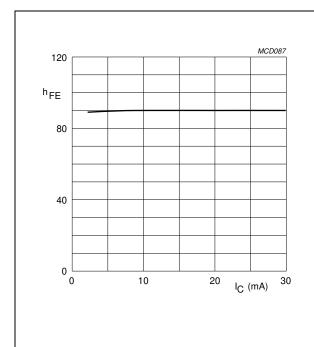
| SYMBOL           | PARAMETER                             | CONDITIONS   | MIN. | TYP. | MAX. | UNIT |
|------------------|---------------------------------------|--|------|------|------|------|
| I <sub>CBO</sub> | collector leakage current             | I <sub>E</sub> = 0; V <sub>CB</sub> = 5 V  | _    | -    | 50   | nA   |
| h <sub>FE</sub>  | DC current gain                       | $I_C = 30 \text{ mA}; V_{CE} = 5 \text{ V}$  | 40   | 90   | _    |      |
| C <sub>c</sub>   | collector capacitance                 | $I_E = i_e = 0$ ; $V_{CB} = 5 \text{ V}$ ; $f = 1 \text{ MHz}$                                     | _    | 0.7  | _    | pF   |
| C <sub>e</sub>   | emitter capacitance                   | $I_C = I_c = 0; V_{EB} = 0.5 V;$<br>f = 1 MHz  | _    | 2.3  | _    | pF   |
| C <sub>re</sub>  | feedback capacitance                  | I <sub>C</sub> = 0; V <sub>CE</sub> = 5 V; f = 1 MHz   | _    | 0.6  | _    | рF   |
| f <sub>T</sub>   | transition frequency                  | I <sub>C</sub> = 30 mA; V <sub>CE</sub> = 5 V;<br>f = 500 MHz                                      | 4    | 5    | _    | GHz  |
| G <sub>UM</sub>  | maximum unilateral power gain; note 1 | I <sub>C</sub> = 30 mA; V <sub>CE</sub> = 8 V;<br>f = 1 GHz; T <sub>amb</sub> = 25 °C              | _    | 13   | _    | dB   |
|                  |                                       | I <sub>C</sub> = 30 mA; V <sub>CE</sub> = 8 V;<br>f = 2 GHz; T <sub>amb</sub> = 25 °C              | _    | 8    | _    | dB   |
| F                | noise figure                          | $I_C = 5 \text{ mA}; V_{CE} = 8 \text{ V};$<br>$f = 1 \text{ GHz}; \Gamma_S = \Gamma_{opt}$        | _    | 1.5  | _    | dB   |
|                  |                                       | $I_C = 5 \text{ mA}; V_{CE} = 8 \text{ V};$<br>$f = 2 \text{ GHz}; \Gamma_S = \Gamma_{\text{opt}}$ | _    | 2.1  | _    | dB   |

Note

<sup>1.</sup>  $G_{UM}$  is the maximum unilateral power gain, assuming  $s_{12}$  is zero and  $G_{UM} = 10 \log \frac{|s_{21}|^2}{(1-|s_{11}|^2)(1-|s_{22}|^2)} dB$ .

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 $V_{CE} = 5 V$ .

Fig.3 DC current gain as a function of collector current; typical values.

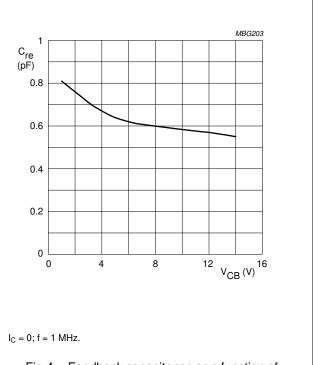
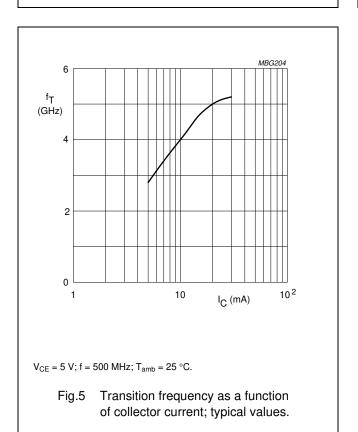


Fig.4 Feedback capacitance as a function of collector-base voltage; typical values.



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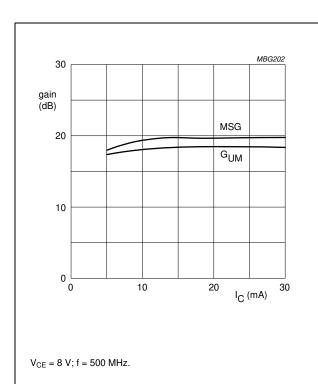


Fig.6 Gain as a function of collector current; typical values.

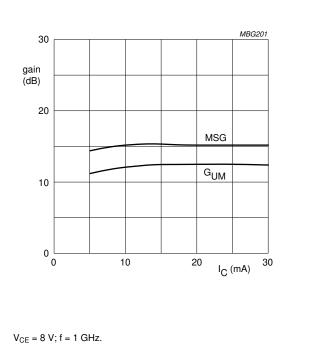
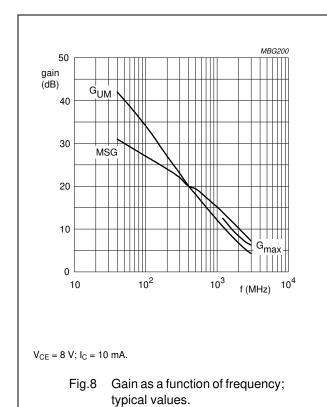
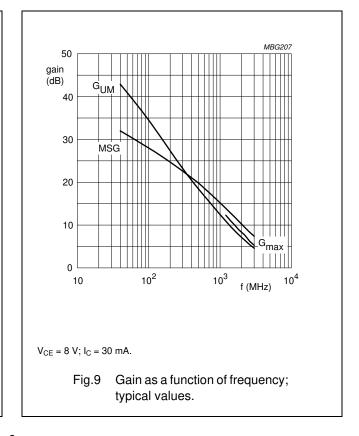


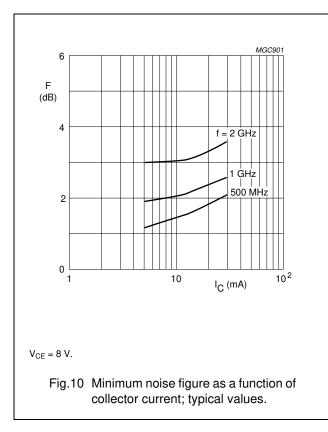
Fig.7 Gain as a function of collector current; typical values.

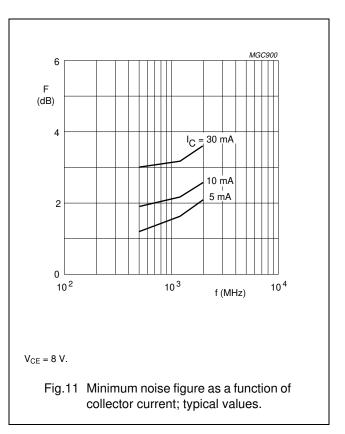


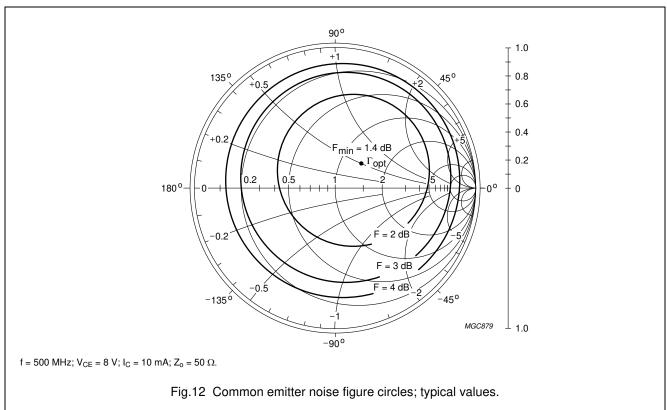


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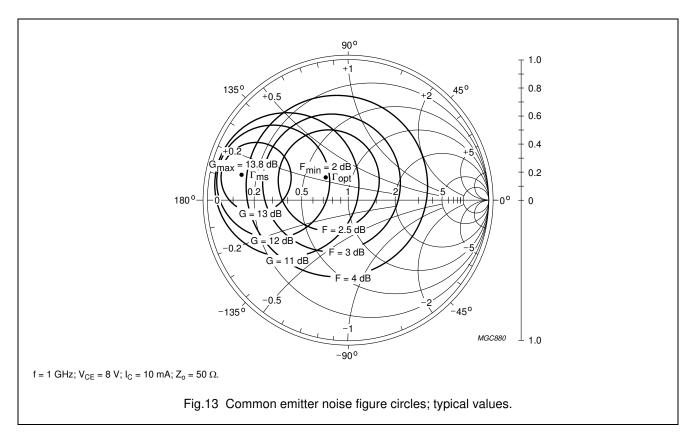


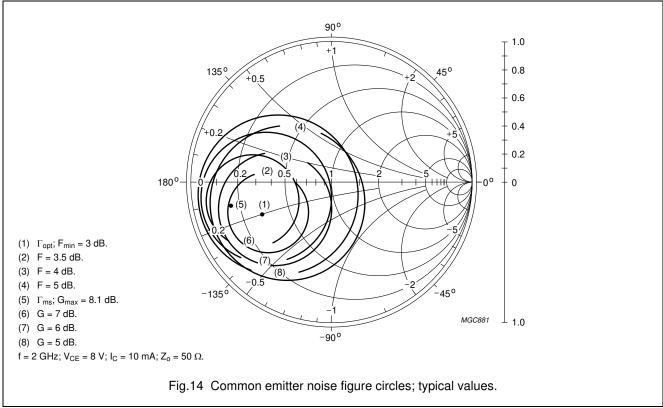




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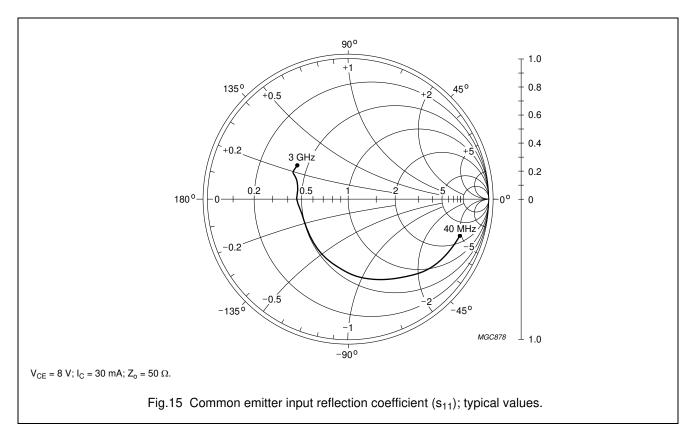


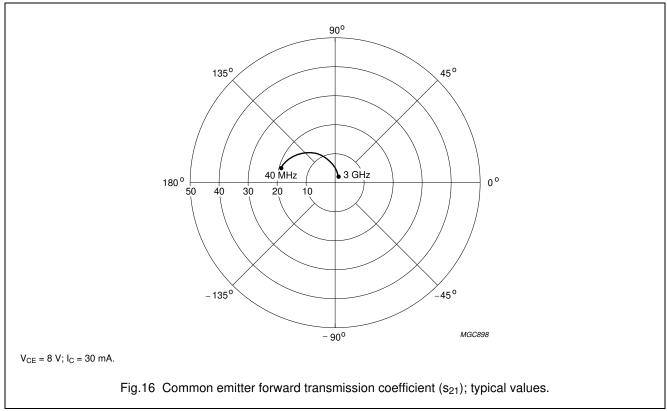
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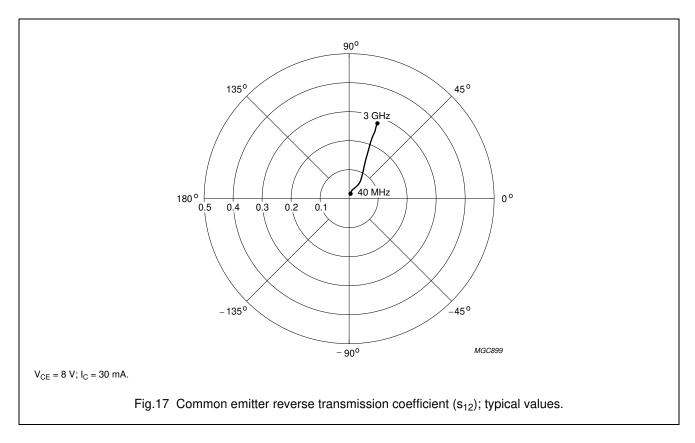
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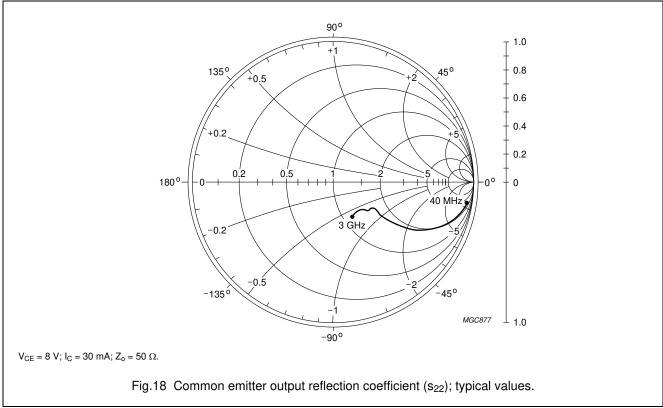




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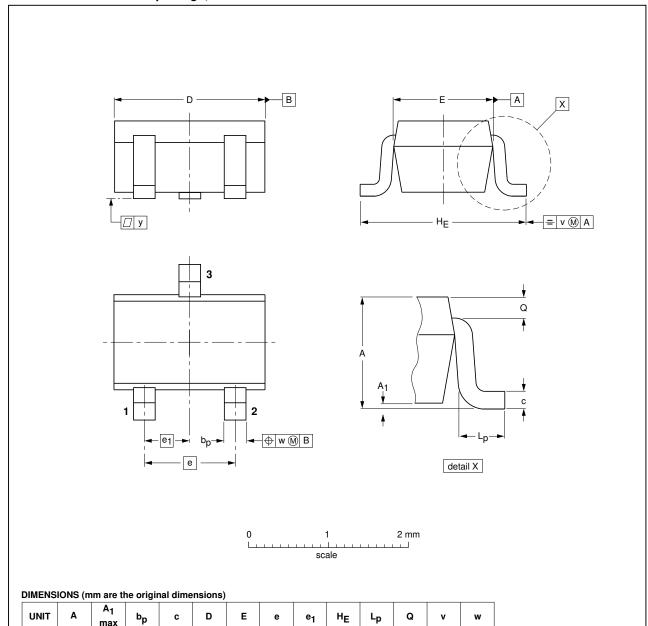
# NPN 5 GHz wideband transistor

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#### **PACKAGE OUTLINE**

#### Plastic surface-mounted package; 3 leads

**SOT323** 



| OUTLINE |     | REFER | RENCES | EUROPEAN   | IOOUE DATE                       |  |
|---------|-----|-------|--------|------------|----------------------------------|--|
| VERSION | IEC | JEDEC | JEITA  | PROJECTION | ISSUE DATE                       |  |
| SOT323  |     |       | SC-70  |            | <del>-04-11-04</del><br>06-03-16 |  |

0.65

0.45

0.23

0.2

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max

0.1

1.1 0.8

mm

0.4 0.3

0.25 0.10

2.2

1.35 1.15

1.3

#### NPN 5 GHz wideband transistor

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| DOCUMENT<br>STATUS(1)  | PRODUCT<br>STATUS <sup>(2)</sup> | DEFINITION  |
|------------------------|----------------------------------|---|
| Objective data sheet   | Development                      | This document contains data from the objective specification for product development. |
| Preliminary data sheet | Qualification                    | This document contains data from the preliminary specification.                       |
| Product data sheet     | Production                       | This document contains the product specification.                                     |

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